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June 2014

FDMC86261P

P-Channel PowerTrench® MOSFET

-150 V, -9 A, 160 m Ω

Features

- Max $r_{DS(on)}$ = 160 m Ω at V_{GS} = -10 V, I_D = -2.4 A
- Max $r_{DS(on)}$ = 185 m Ω at V_{GS} = -6 V, I_D = -2.2 A
- Very low RDS-on mid voltage P channel silicon technology optimised for low Qg
- This product is optimised for fast switching applications as well as load switch applications
- 100% UIL Tested
- RoHS Compliant



General Description

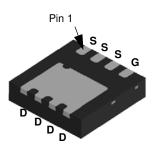
This P-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® technology. This very high density process is especially tailored to minimize on-state resistance and optimized for superior switching performance.

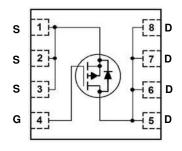
Applications

- Active Clamp Switch
- Load Switch

Top Bottom







MLP 3.3x3.3

MOSFET Maximum Ratings TA = 25 °C unless otherwise noted

Symbol	Parameter			Ratings	Units
V_{DS}	Drain to Source Voltage			-150	V
V_{GS}	Gate to Source Voltage			±25	V
	Drain Current -Continuous	T _C = 25 °C		-9	
I_D	-Continuous T _A = 25 °C (Note 1a)		(Note 1a)	-2.7	Α
	-Pulsed			-20	
E _{AS}	Single Pulse Avalanche Energy		(Note 3)	121	mJ
В	Power Dissipation	T _C = 25 °C		40	W
P_D	Power Dissipation	T _A = 25 °C	(Note 1a)	2.3	VV
T _J , T _{STG}	Operating and Storage Junction Tempera	ture Range		-55 to + 150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	3.1	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1	a) 53	C/VV

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC86261P	FDMC86261P	Power 33	13"	12 mm	3000 units

Electrical Characteristics T_J = 25 °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	octeristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = -250 \mu A, V_{GS} = 0 V$	-150			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I_D = -250 μ A, referenced to 25 °C		-132		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -120 V, V _{GS} = 0 V			-1	μΑ
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA

On Characteristics

V _{GS(th)}	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = -250 \mu A$	-2	-3	-4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = -250 μ A, referenced to 25 °C		6		mV/°C
		$V_{GS} = -10 \text{ V}, I_D = -2.4 \text{ A}$		130	160	
r _{DS(on)}	Static Drain to Source On Resistance	$V_{GS} = -6 \text{ V}, I_D = -2.2 \text{ A}$		141	185	$m\Omega$
, ,		$V_{GS} = -10 \text{ V}, I_D = -2.4 \text{ A}, T_J = 125 \text{ °C}$		218	269	
9 _{FS}	Forward Transconductance	$V_{DS} = -10 \text{ V}, I_{D} = -2.4 \text{ A}$		9		S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 75 V V 0 V		1021	1360	рF
Coss	Output Capacitance	$V_{DS} = -75 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1 MHz		87	120	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 101112		4.7	10	pF
R_{q}	Gate Resistance		0.1	1.7	3.4	Ω

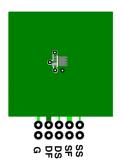
Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time		11	20	ns
t _r	Rise Time	V _{DD} = -75 V, I _D = -2.4 A,	2.4	10	ns
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = -10 \text{ V}, R_{GEN} = 6 \Omega$	18	33	ns
t _f	Fall Time		9.2	20	ns
$Q_{g(TOT)}$	Total Gate Charge	V _{GS} = 0 V to -10 V	17	24	nC
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0 \text{ V to -6 V}$ $V_{DD} = -75 \text{ V},$ $I_{D} = -2.4 \text{ A}$	11	16	nC
Q_{gs}	Total Gate Charge	I _D = -2.4 A	4.2		nC
Q_{gd}	Gate to Drain "Miller" Charge		3.7		nC

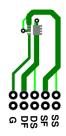
Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = -2.4 \text{ A}$ (Note 2)		-0.81	-1.3	V
	Source to Drain blode 1 of ward voltage	V _{GS} = 0 V, I _S = -1.9 A (Note 2)	-0.80	-1.2	V	
t _{rr}	Reverse Recovery Time	I _F = -2.4 A, di/dt = 100 A/μs		81	130	ns
Q _{rr}	Reverse Recovery Charge			197	315	nC

^{1.} R_{8JA} is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R_{8JC} is guaranteed by design while R_{8CA} is determined by the user's board design.



a) 53 °C/W when mounted on a 1 in² pad of 2 oz copper



b) 125 °C/W when mounted on a minimum pad of 2 oz copper

- 2. Pulse Test: Pulse Width < 300 μ s, Duty cycle < 2.0%.
- 3. Starting $T_J = 25$ °C; P-ch: L = 3 mH, $I_{AS} = -9$ A, $V_{DD} = -150$ V, $V_{GS} = -10$ V. 100% test at L = 0.1 mH, $I_{AS} = -28$ A.

Typical Characteristics T_{.1} = 25 °C unless otherwise noted

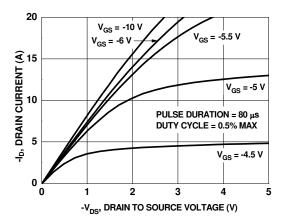


Figure 1. On Region Characteristics

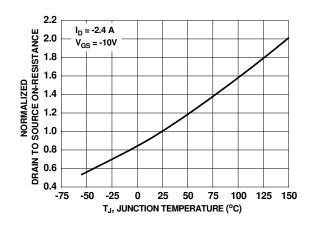


Figure 3. Normalized On Resistance vs Junction Temperature

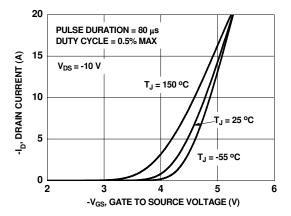


Figure 5. Transfer Characteristics

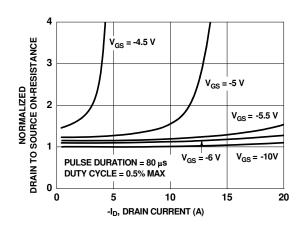


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

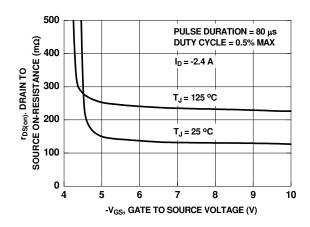


Figure 4. On-Resistance vs Gate to Source Voltage

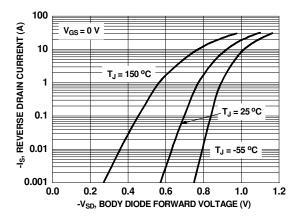


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25$ °C unless otherwise noted

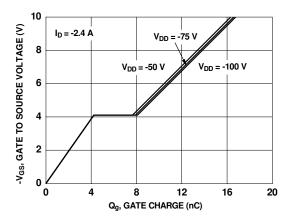


Figure 7. Gate Charge Characteristics

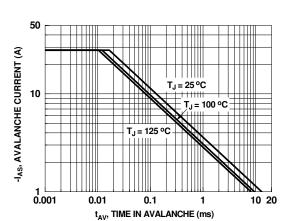


Figure 9. Unclamped Inductive Switching Capability

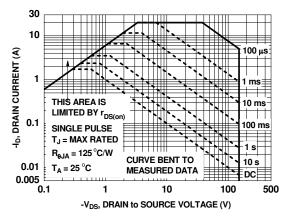


Figure 11. Forward Bias Safe Operating Area

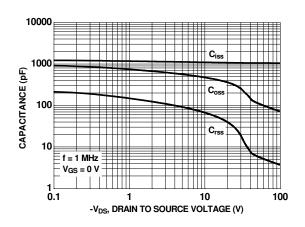


Figure 8. Capacitance vs Drain to Source Voltage

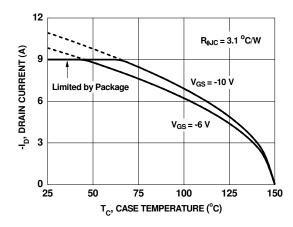


Figure 10. Maximum Continuous Drain Current vs Case Temperature

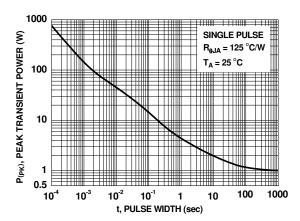


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25 °C unless otherwise noted

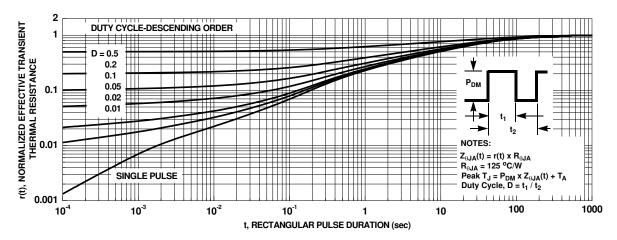
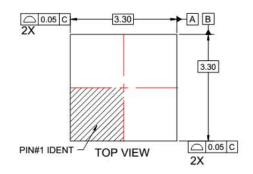
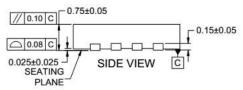
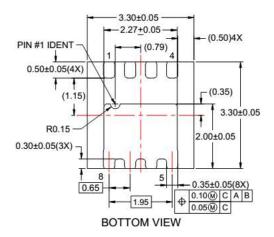


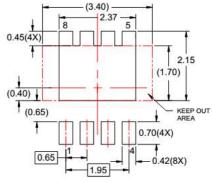
Figure 13. Junction-to-Ambient Transient Thermal Response Curve

Dimensional Outline and Pad Layout









RECOMMENDED LAND PATTERN

NOTES:

- A. DOES NOT CONFORM TO JEDEC REGISTRATION MO-229
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.
- E. DRAWING FILENAME: MKT-MLP08Srev3.



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Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
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